

Power MOSFET

■ GENERAL DESCRIPTION

The XP131A1330SR is an N-channel Power MOSFET with low on-state resistance and ultra high-speed switching characteristics

Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.

The small SOP-8 package makes high density mounting possible.

■ APPLICATIONS

- Notebook PCs
- Cellular and portable phones
- On-board power supplies
- Li-ion battery systems

■ FEATURES

Low On-State Resistance: $R_{ds(on)}=0.03\Omega$ ($V_{gs}=4.5V$)

: $R_{ds(on)} = 0.04 \, \Omega$ ($V_{gs} = 2.5V$)

: $R_{ds(on)} = 0.07 \, \Omega$ ($V_{gs} = 1.5V$)

Ultra High-Speed Switching

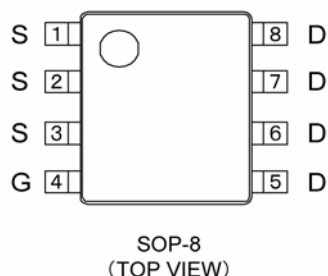
Driving Voltage : 1.5V

N-Channel Power MOSFET

DMOS Structure

Package : SOP-8

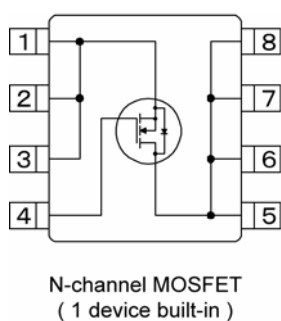
■ PIN CONFIGURATION



PIN ASSIGNMENT

PIN NUMBER	PIN NAME	FUNCTION
1~3	S	Source
4	G	Gate
5~8	D	Drain

■ EQUIVALENT CIRCUIT



■ ABSOLUTE MAXIMUM RATINGS

 $T_a = 25^\circ\text{C}$

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	V _{dss}	20	V
Gate-Source Voltage	V _{gss}	±8	V
Drain Current (DC)	I _d	8	A
Drain Current (Pulse)	I _{dp}	30	A
Reverse Drain Current	I _{dr}	8	A
Channel Power Dissipation *	P _d	2.5	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

* When implemented on a glass epoxy PCB

ELECTRICAL CHARACTERISTICS

DC Characteristics

Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain Cut-Off Current	Idss	Vds=20V, Vgs=0V	-	-	10	μA
Gate-Source Leak Current	Igss	Vgs=±8V, Vds=0V	-	-	±1	μA
Gate-Source Cut-Off Voltage	Vgs(off)	Id=1mA, Vds=10V	0.5	-	1.2	V
Drain-Source On-State Resistance *	Rds(on)	Id=4A, Vgs=4.5V	-	0.025	0.03	Ω
		Id=4A, Vgs=2.5V	-	0.030	0.040	Ω
		Id=1A, Vgs=1.5V	-	0.045	0.07	Ω
Forward Transfer Admittance *	Yfs	Id=4A, Vds=10V	-	22	-	S
Body Drain Diode Forward Voltage	Vf	If=8A, Vgs=0V	-	0.85	1.1	V

* Effective during pulse test.

Dynamic Characteristics

Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Capacitance	Ciss	Vds=10V, Vgs=0V f=1MHz	-	950	-	pF
Output Capacitance	Coss		-	430	-	pF
Feedback Capacitance	Crss		-	180	-	pF

Switching Characteristics

Ta = 25°C

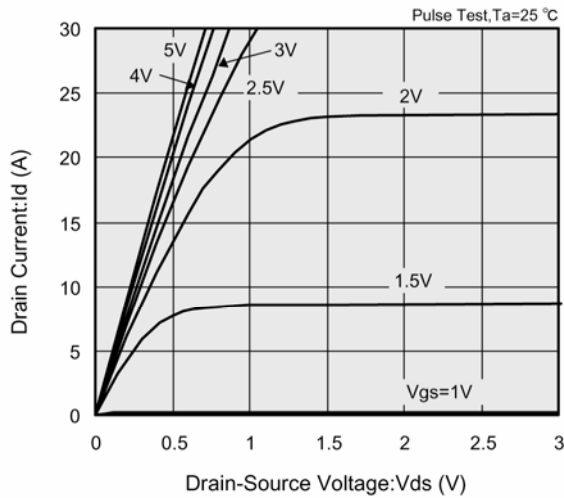
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-On Delay Time	td (on)	Vgs=5V, Id=4A Vdd=10V	-	15	-	ns
Rise Time	tr		-	20	-	ns
Turn-Off Delay Time	td (off)		-	80	-	ns
Fall Time	tf		-	15	-	ns

Thermal Characteristics

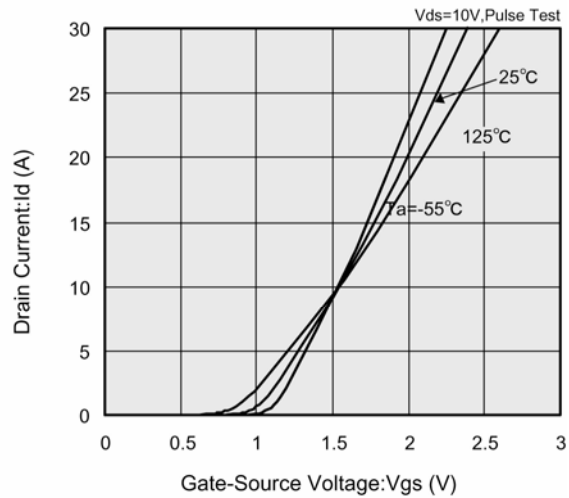
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal Resistance (Channel-Ambience)	Rth (ch-a)	Implement on a glass epoxy resin PCB	-	50	-	°C/W

TYPICAL PERFORMANCE CHARACTERISTICS

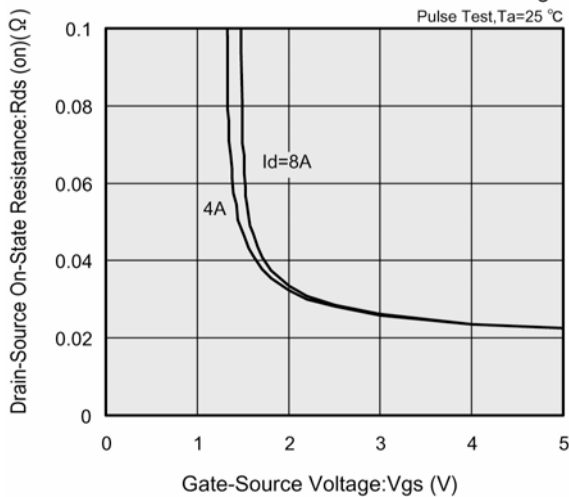
(1) Drain Current vs. Drain-Source Voltage



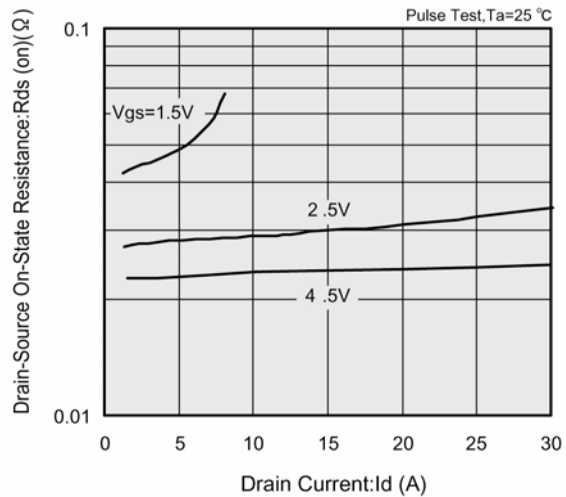
(2) Drain Current vs. Gate-Source Voltage



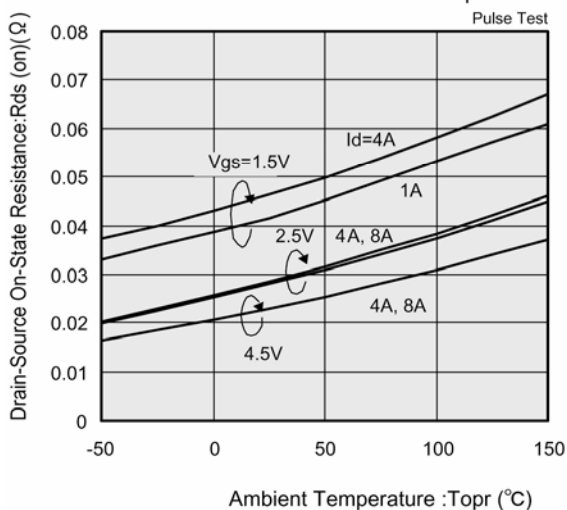
(3) Drain-Source On-State Resistance vs. Gate-Source Voltage



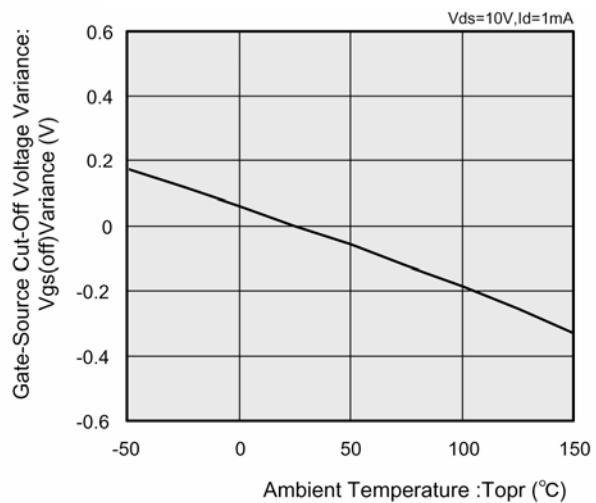
(4) Drain-Source On-State Resistance vs. Drain Current



(5) Drain-Source On-State Resistance vs. Ambient Temperature

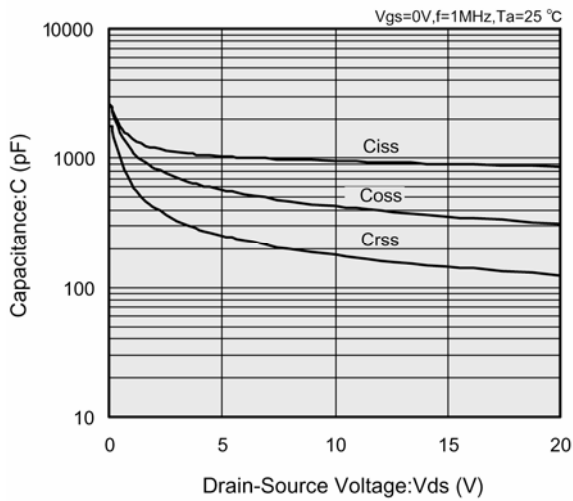


(6) Gate-Source Cut-Off Voltage Variance vs. Ambient Temperature

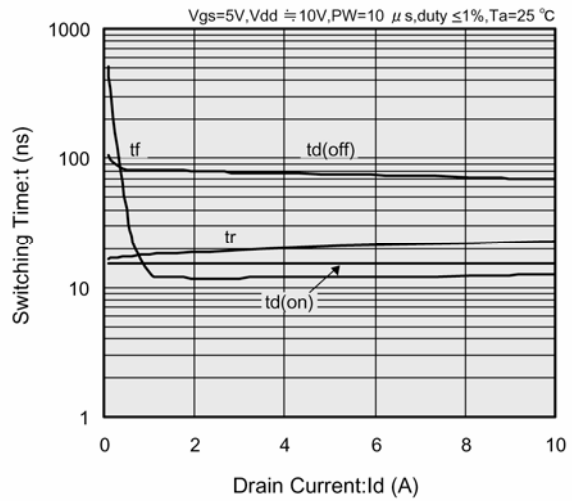


TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

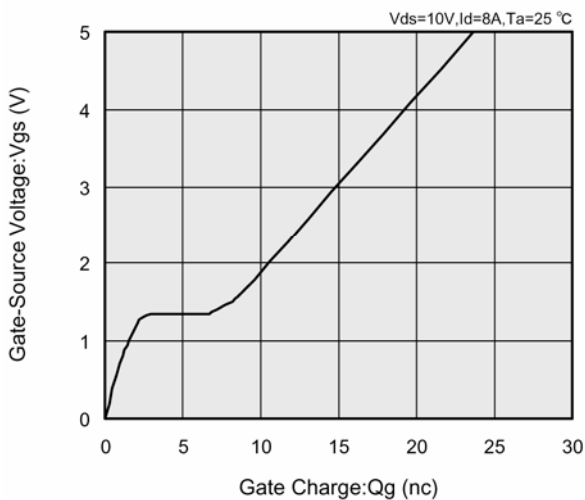
(7) Capacitance vs. Drain-Source Voltage



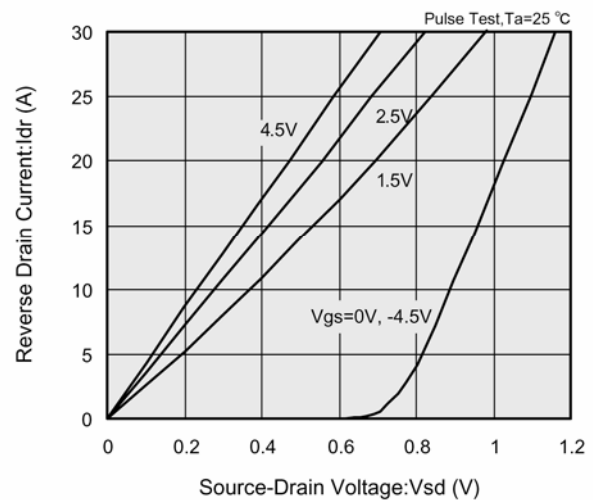
(8) Switching Time vs. Drain Current



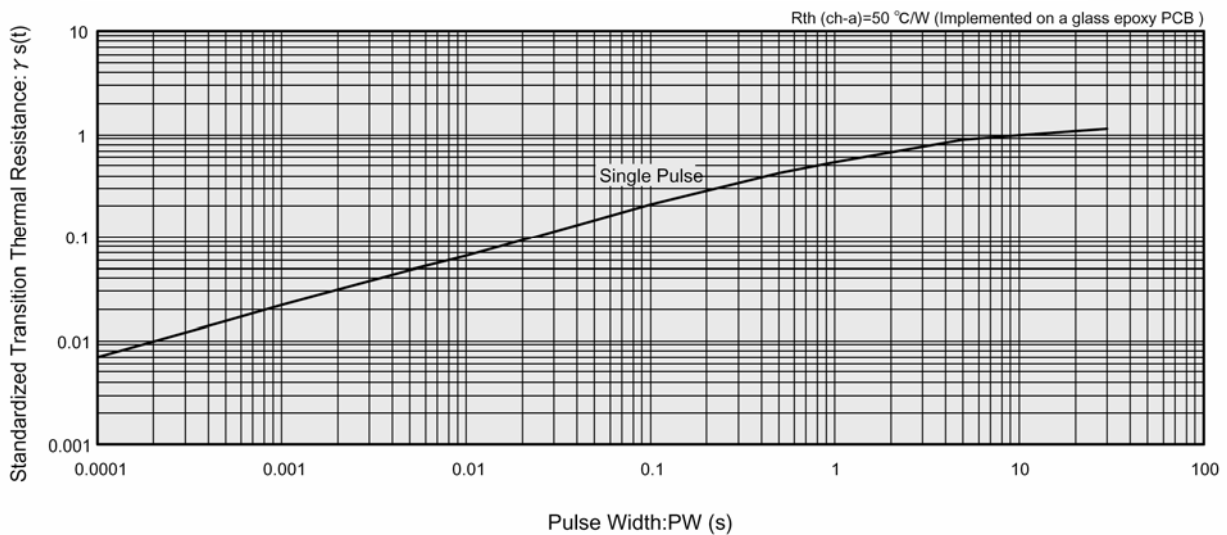
(9) Gate-Source Voltage vs. Gate Charge



(10) Reverse Drain Current vs. Source-Drain Voltage



(11) Standardized transition Thermal Resistance vs. Pulse Width



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